

In the Claims

1. (currently amended) A chemical vapor deposition apparatus comprising:
a deposition chamber defined partly by a chamber wall lid and a chamber body
having similar thicknesses, the chamber wall lid or body having an innermost surface
inside the chamber and an outermost surface outside the chamber; and
a valve body having a seat between the innermost and outermost surfaces of the
chamber wall lid or body.

2. (currently amended) The apparatus of claim 1 wherein the chemical
vapor deposition apparatus comprises an atomic layer deposition apparatus.

3. (currently amended) The apparatus of claim 1 wherein the ~~chamber wall~~
~~comprises a~~ seat is between the innermost and outermost surfaces of the chamber lid.

4. (currently amended) The apparatus of claim 1 wherein the valve body
includes a portion of the chamber wall lid or body as at least a part of the seat.

5. (currently amended) The apparatus of claim 1 wherein the valve body
comprises at least a part of a valve housing between the innermost and outermost
surfaces of the chamber wall lid or body.

6. (currently amended) The apparatus of claim 5 wherein the valve body includes a portion of the chamber ~~wall~~ lid or body as at least a part of the valve housing.

7. (currently amended) The apparatus of claim 1 further comprising at least a part of a process chemical inlet to the valve body between the innermost and outermost surfaces of the chamber ~~wall~~ lid or body.

8. (currently amended) The apparatus of claim 7 wherein the chamber ~~wall~~ lid or body forms at least a part of the chemical inlet.

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9. (currently amended) A chemical vapor deposition apparatus comprising:
a deposition chamber having a single thickness lid;
a process chemical opening completely through the lid; and
an isolation mechanism proximate the chemical opening, the lid being integral to the isolation mechanism and the isolation mechanism selectively isolating the deposition chamber from receiving material through the chemical opening.

10. (original) The apparatus of claim 9 wherein the chemical vapor deposition apparatus comprises an atomic layer deposition apparatus.

11. (original) The apparatus of claim 9 wherein the isolation mechanism comprises a valve.

12. (original) The apparatus of claim 11 wherein the lid comprises at least a part of a seat of the valve.

13. (original) The apparatus of claim 11 wherein the lid comprises at least a part of a housing of the valve.

14. (original) The apparatus of claim 11 wherein the lid comprises at least a part of a process chemical inlet to the valve.

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15. (original) A chemical vapor deposition apparatus comprising:
a deposition chamber having a lid; and
a valve body including a portion of the lid as part of the valve body, the valve body selectively shutting off flow of a process chemical into the chamber, adjusting the flow rate of the chemical into the chamber, or both.

16. (original) The apparatus of claim 15 wherein the chemical vapor deposition apparatus comprises an atomic layer deposition apparatus.

17. (original) The apparatus of claim 15 wherein at a 50% open position as indicated by a stem position the valve body provides a flow rate of no more than about 50% of a maximum flow rate through the valve body.

18. (original) The apparatus of claim 15 wherein the portion of the lid comprises at least a part of a valve housing.

19. (original) The apparatus of claim 18 wherein the part of the valve housing comprised by the portion of the lid is defined by a cylindrical opening in the lid, the valve body further comprising a stem coincident with a central axis of the cylindrical opening and positioned at least partially within the cylindrical opening.

20. (original) The apparatus of claim 15 wherein the portion of the lid comprises at least a part of a valve seat.

At
or 21. (original) The apparatus of claim 20 wherein the entirety of the valve seat is between an innermost surface of the lid inside the chamber and an outermost surface of the lid outside the chamber.

22. (original) The apparatus of claim 20 wherein the valve seat comprises a plug seat or a diaphragm seat.

23. (original) The apparatus of claim 20 wherein the part of the valve seat comprised by the portion of the lid is defined by a beveled lid surface around a cylindrical opening through the lid, the valve body further comprising a plug complementary to the beveled lid surface.

24. (original) The apparatus of claim 20 wherein the part of the valve seat comprised by the portion of the lid is defined by an annular platform around a cylindrical opening through the lid, the valve body further comprising a plug and a diaphragm between the plug and annular platform.

At 25. (original) The apparatus of claim 15 wherein the portion of the lid comprises at least a part of a process chemical inlet in the valve body.

26. (original) The apparatus of claim 25 wherein the apparatus further comprises a process chemical inlet through the lid to the chemical inlet in the valve body.

27. (original) A chemical vapor deposition apparatus comprising:

a deposition chamber having a lid, the lid having an inner surface inside the chamber, an outer surface outside the chamber, and an opening defined by sidewalls extending between the inner and outer surfaces;

a valve body having a housing and a seat;

at least a part of the housing comprising at least a part of the outer surface of the lid, at least a part of the opening sidewalls of the lid, or both; and

at least a part of the seat comprising at least a part of the inner surface of the lid, at least a part of the opening sidewalls of the lid, or both.

28. (original) The apparatus of claim 27 wherein the chemical vapor deposition apparatus comprises an atomic layer deposition apparatus.

29. (original) The apparatus of claim 27 further comprising a process chemical inlet to the valve body, a lid portion between the inner surface and the outer surface forming at least a part of the chemical inlet.